

## Pat nt Abstracts f Japan

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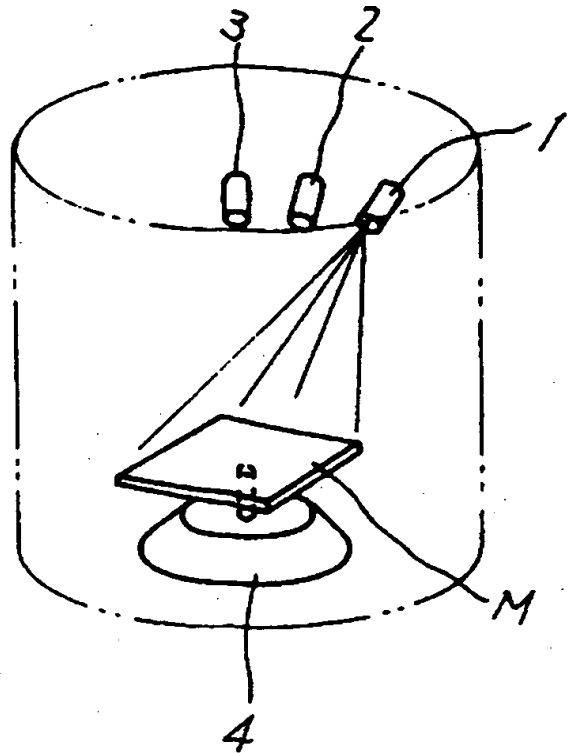
APPLICATION DATE : 25-12-81  
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TITLE : DEVELOPING METHOD



**ABSTRACT :** PURPOSE: To reduce the small-dimension variations among portions in a mask and chips in a wafer, by preparing two or more developers various in concentration, and successively using them in order of concentration, i.e. from the thick to the thin.

**CONSTITUTION:** A mask M coated with a photoresist as well as subjected to a pattern lithography is secured onto a spinner 4 and is stationary or rotating. A thick developer is applied to the mask M from a nozzle 1 by the spray or shower system. when a time  $t_1$  has elapsed, a thin developer is supplied from a nozzle 2, and further at a time  $t_2$ , a rinsing pure water is supplied from a nozzle 3. Since the developers various in concentration are prepared and used in order of concentration, from the thick to the thin, it is possible to obtain various effects offered by the thin developer conjointly with the high-speed developing effect by the thick developer.

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